

#### N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Ι <sub>D</sub>
- (BK)D33	· -D3(ON)	T <sub>A</sub> = 25℃
600V	160Ω @ V <sub>GS</sub> = 10V	70mA

### **Description and Applications**

This new generation uses advanced planar technology MOSFET, provide excellent high Voltage and fast switching, making it ideal for small-Signal and level shift applications.

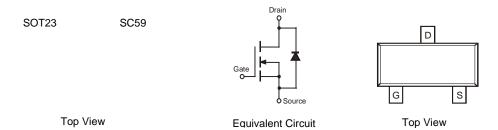
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

#### **Features and Benefits**

- Low Input Capacitance
- High BVDss rating for power application
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

#### **Mechanical Data**

- Case: SC59 / SOT23
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



#### **Ordering Information (Note 3)**

Part Number	Case	Packaging
BSS127SSN-7	SC59	3000/Tape & Reel
BSS127S-7	SOT23	3000/Tape & Reel

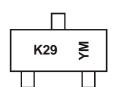
Notes:

1. No purposefully added lead.

SOT23

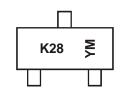
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



K29 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)



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SC59

Date Code Kev

Date Code Itoy												
Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ	7	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings**

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V <sub>DSS</sub>	600	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25℃ T <sub>A</sub> = 70℃	ID	50 40	mA
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25℃ T <sub>A</sub> = 70℃	I <sub>D</sub>	70 55	mA
Continuous Drain Current (Note 4) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = 25℃ T <sub>A</sub> = 70℃	I <sub>D</sub>	45 35	mA
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = 25℃ T <sub>A</sub> = 70℃	I <sub>D</sub>	65 50	mA
Pulsed Drain Current @ T <sub>SP</sub> = 25℃ (Notes 6)	I <sub>DM</sub>	0.16	А		

# **Thermal Characteristics**

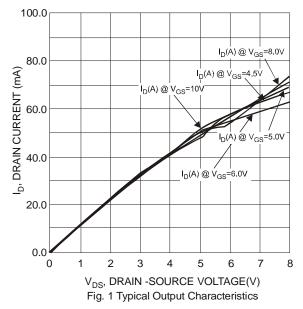
Characteristic	Symbol	Value	Units
Power Dissipation, @T <sub>A</sub> = 25℃ (Note 4)	$P_{D}$	0.61	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25℃ (Note 4)	$R_{ heta JA}$	204	°C/W
Power Dissipation, @T <sub>SP</sub> = 25℃ (Note 5)	$P_{D}$	1.25	W
Thermal Resistance, Junction to Ambient @T <sub>SP</sub> = 25℃ (Note 5)	$R_{\theta JSA}$	100	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

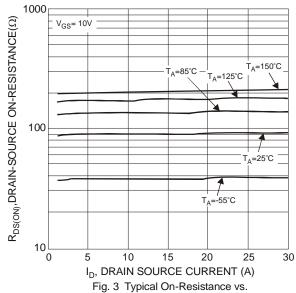
# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	600		-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25℃	I <sub>DSS</sub>	-	-	0.1	μA	$V_{DS} = 600V, V_{GS} = 0V$	
Gate-Body Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	3	-	4.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		-	80	160		$V_{GS} = 10V, I_D = 16mA$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	-	95	190	Ω	$V_{GS} = 5.0V, I_D = 16mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	76	-	mS	$V_{DS} = 10V, I_{D} = 16mA$	
Diode Forward Voltage	$V_{SD}$	-	-	1.5	V	$V_{GS} = 0V$ , $I_S = 16mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	21.8	-			
Output Capacitance	Coss	-	2.2	-	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	0.3	-			
Total Gate Charge	Qg	-	1.08	-		101/11/ 2001/	
Gate-Source Charge	$Q_{gs}$	-	0.08	-	nC	$V_{GS} = 10V, V_{DD} = 300V,$	
Gate-Drain Charge	$Q_{gd}$	-	0.50	-		$I_D = 0.01A$	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.0	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	7.2	-	ns	$V_{DD} = 300V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.7	-	ns	$R_{GEN} = 6\Omega$ ,	
Turn-Off Fall Time	t <sub>f</sub>	-	168	-	ns	$I_D = 10$ mA	
Reverse Recovery Time	T <sub>rr</sub>	-	131	-	ns	V <sub>R</sub> =300 V, I <sub>F</sub> =0.016 A,	
Reverse Recovery Charge	Q <sub>rr</sub>	-	32	-	nC	di/dt = 100A/µs	

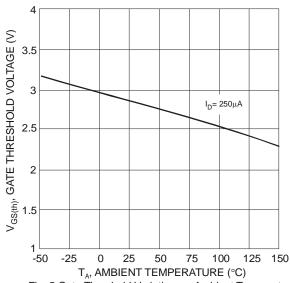
- 4. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
  Repetitive rating, pulse width limited by junction temperature, 10μs pulse, duty cycle = 1%.
  Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



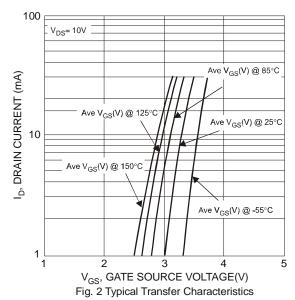




Drain Current and Temperature







250 200 150

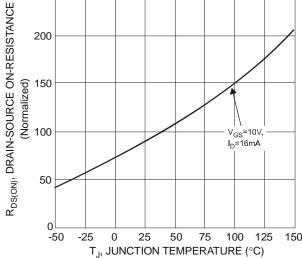
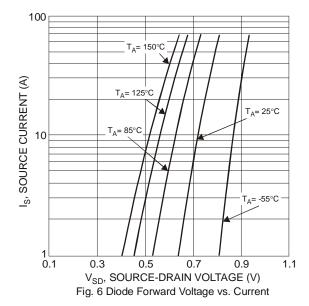
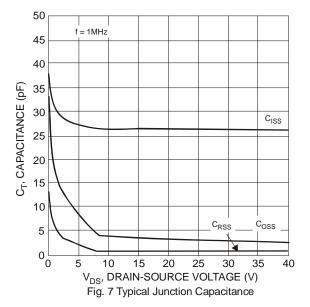


Fig. 4 On-Resistance Variation with Temperature







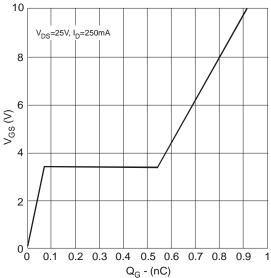
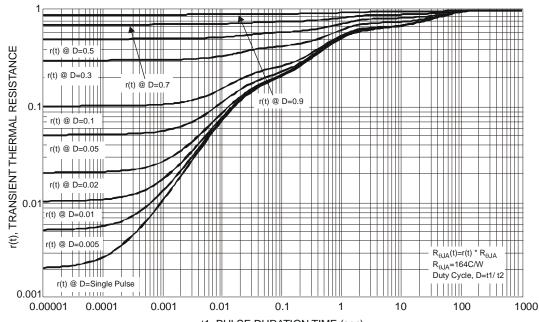


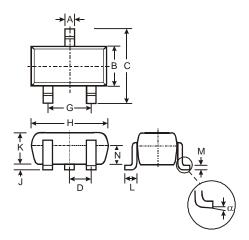
Fig. 8 Gate Charge Characteristics



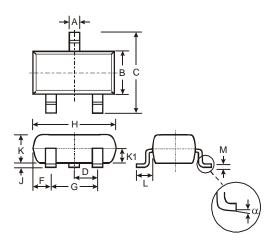
t1, PULSE DURATION TIME (sec) Fig. 9 Transient Thermal Resistance



# **Package Outline Dimensions**



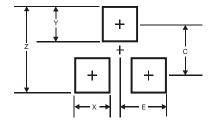
SC59					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	-	-	0.95		
G	-	-	1.90		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
N	0.70	0.80	0.75		
α	0°	8°	-		
All	Dimens	ions in	mm		



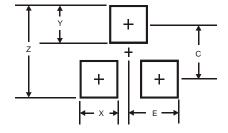
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
C	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Η	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					



### **Suggested Pad Layout**



SOT23			
Dimensions   Value (in mm)			
Z	2.9		
Х	0.8		
Y	0.9		
С	2.0		
E	1.35		



SC59			
Dimensions	Value (in mm)		
Z	3.4		
Х	0.8		
Υ	1.0		
С	2.4		
E	1.35		

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